

Workshop on quantum dot based devices for long wavelength sources and single photon sources

CNRS/LPN Marcoussis
10th-11th February 2005

Thursday

- 11:00 – 11:20 *Presentation of LPN* (Jean-Yves Marzin, Director)
- 11:20 – 11:30 *Device activities within SANDiE: JPR-A, JPR-C, Reporting-form* (A Ramdane, A Shields)
- 11:30 – 12:00 *Quantum dots for tuneable lasers* (David Childs, Bookham)
- 12:00 – 12:30 *Telecom wavelength single photon sources* (Martin Ward, Toshiba Europe)
- Lunch
- 14:00 – 14:30 *Memory of a GaAs/(AlGa)As field effect transistor incorporating quantum dots* (Richard Hill, University of Nottingham)
- 14:30 – 15:00 *Long-wavelength In(Ga)As/GaAs quantum dot based lasers grown by MOVPE* (Guillaume Saint Girons, LPN)
- 15:00 – 15:30 *1.3 μm InGaAs/GaAs Quantum dot Devices: VCSEL, Edge Emitter and Amplifier* (Friedhelm Hopfer, University of Berlin)
- 15:30 – 16:30 Coffee break
Discussions

Friday

- 9:00 – 9:30 *Development of 1.3 μm quantum dot lasers and 1.0 μm and 1.3 μm single photon sources* (David Mowbray, University of Sheffield)
- 9:30 – 10:00 *InAs/InP (311)B quantum dot active medium for 1.55 μm telecommunication devices* (Nicolas Bertru, INSA-LENS Rennes)
- 10 :00 – 10 :30 *MBE grown InAs/GaAs QD lasers and amplifiers* (Anthony Martinez, LPN)